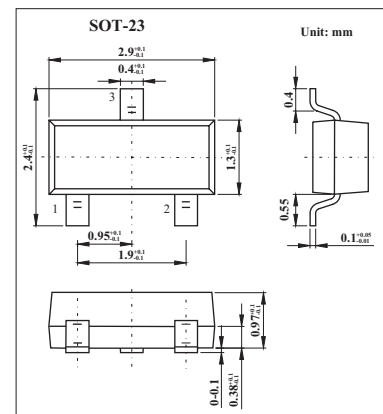


## Silicon PIN Diodes

## BA779;BA779S

## ■ Features

- Wide frequency range 10 MHz to 1 GHz

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Value	Unit
Reverse Voltage	$V_R$		30	V
Forward Current	$I_F$		50	mA
Junction Temperature	$T_j$		125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$		-55 to +125	$^\circ\text{C}$
Junction ambient	$R_{thJA}$	on PC board 50mm×50mm×1.6mm	500	K/W

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	$V_F$	$I_F = 20\text{ mA}$			1	V
Reverse Current	$I_R$	$V_R = 30\text{ V}$			50	nA
Diode capacitance	$C_D$	$f = 100\text{ MHz}, V_R = 0$			0.5	pF
Differential forward resistance	$r_f$	$f = 100\text{ MHz}, I_F = 1.5\text{ mA}$			50	$\Omega$
Reverse impedance	$z_r$	$f = 100\text{ MHz}, V_R = 0$	5			K $\Omega$
			9			
Minority carrier lifetime	$\tau$	$I_F = 10\text{ mA}, I_R = 10\text{ mA}$		4		$\mu\text{ S}$